**Solid State Devices** 



# Section 16 Recombination & Generation 16.6 SRH formula adapted to interface states

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For single level bulk traps ....

$$R_{bulk} = \frac{np - n_i^2}{\frac{1}{c_p N_T} (n + n_1) + \frac{1}{c_n N_T} (p + p_1)} = \frac{(np - n_i^2) N_T}{\frac{1}{c_p} (n + n_1) + \frac{1}{c_n} (p + p_1)}$$



For single level interface trap at E ...

$$R(E) = \frac{\left(n_{s} p_{s} - n_{i}^{2}\right) D_{T}(E) dE}{\frac{1}{c_{ps}} \left(n_{s} + n_{1s}\right) + \frac{1}{c_{ns}} \left(p_{s} + p_{1s}\right)}$$

$$R = \int_{E_V}^{E_C} R(E) \, dE$$

All surface recombination goes through one step => single integral





#### **Case 1: Minority Carrier Recombination**





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Consider the Denominator ... close to  $E_F$ 





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doped









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## Case 1: Minority Carrier Recombination

Donor doped

$$W(E) = 1 + \frac{n_i e^{(E-E_i)\beta}}{N_D} + \frac{c_{ps}}{c_{ns}} \frac{n_i e^{-(E-E_i)\beta}}{N_D} \qquad 1 = \frac{c_{ps}}{c_{ns}} \frac{n_i}{N_D} e^{-(E_{Pr}-E_i)\beta}$$

$$E_{Fr} \in \widetilde{E_Fr} + \Delta E$$

$$\widetilde{W}(E) = \begin{cases} 1 & \text{for } E_{Fr} \leq E \leq E_F \\ \infty & \text{otherwise} \end{cases} \qquad (E_i - \widetilde{E_{Fr}}) = (E_F - E_i)$$

$$e^{\Delta E\beta} = \frac{c_{ps}}{c_{ns}}$$

$$R = \int_{E_V}^{E_C} R(E) dE \qquad R \approx \int_{E_{F'}}^{E_F} c_{ps} \Delta p_{s0} D_{IT}(E) dE$$
Ready to evaluate this integral
$$W = \int_{E_V}^{E_{F'}} E_i = E_F E_C$$







These approximations gave critical insights in the 1950s



These approximations gave critical insights in the 1950s



#### Now let's evaluate this integral

$$R \approx \int_{E_{F'}}^{E_{F}} c_{ps} \Delta p_{s0} D_{IT}(E) dE$$

$$R \approx (E_F - E'_F) c_{ps} D_{IT} \Delta p_{s0}$$

$$R = \frac{s_g}{\Delta p_{s0}}$$

$$s_g \approx (E_F - E'_F) c_{ps} D_{IT}$$

Surface recombination velocity Experimental fitting/ measurement! Quality of surface and process Industry: Process control



How important is  $\Delta E \approx \pm 2.3 k_B T \approx 0.060 eV$ 

### Surface Recombination Velocity



# $R \approx \int_{E_F'}^{E_F} c_{ps} \Delta p_{s0} D_{IT}(E) dE$ $R \approx (E_F - E'_F) c_{ps} D_{IT} \Delta p_{s0}$ $R = s_g \Delta p_{s0}$

$$s_g \approx (E_F - E'_F)c_{ps}D_{IT}$$

Surface recombination velocity Experimental fitting/ measurement! Quality of surface and process Industry:

Process control

Research:

Developing new materials & processes

## What does $D_{IT}(E)$ look like?





How many dangling bonds?



<u>STM</u> image of the first (<u>4×4</u>) and second layers ( $\sqrt{3}\times\sqrt{3}-\beta$ ) of silicene grown on a thin silver film. Image size 16×16 nm.



